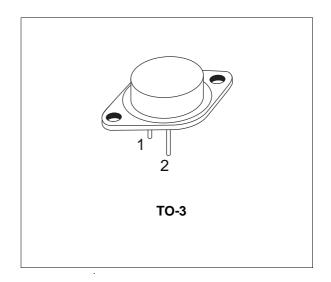


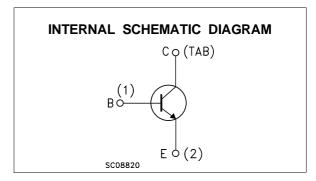
HIGH CURRENT NPN SILICON TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR

DESCRIPTION

The 2N5038 is a silicon planar multiepitaxial NPN transistors in Jedec TO-3 metal case. They are especially intended for high current and switching applications.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	150	V
V _{CEX}	Collector-Emitter Voltage (V_{BE} =-1.5 V R_{BE} =100 Ω)	150	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} < 50\Omega$)	110	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	90	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
Ic	Collector Current	20	А
I _{CM}	Collector Peak Current	30	А
I _B	Base Current	5	А
P _{tot}	Total Dissipation at T _c ≤ 25 °C	140	W
T _{stg}	Storage Temperature	-65 to 200	°C

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THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Max	1.25	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

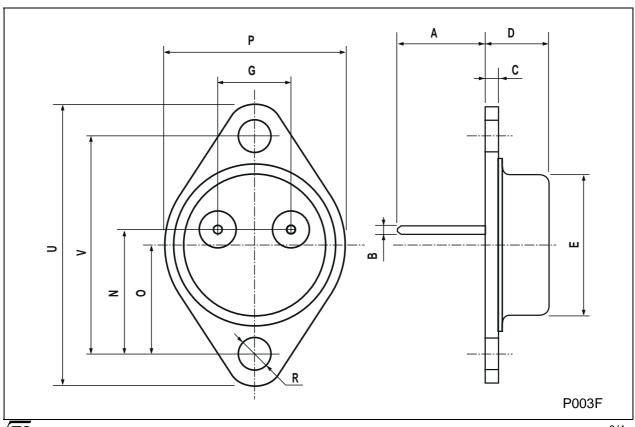
Parameter Test Conditions		Min.	Тур.	Max.	Unit
Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 140 V V _{CE} = 100 V T _c = 150 °C			50 10	mA mA
Collector Cut-off Current (I _B = 0)	V _{CE} = 70 V			20	mA
Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V V _{EB} = 5 V			50 5	mA mA
Collector-Emitter Sustaining Voltage	I _C = 0.2 A	90			V
Collector-Emitter Sustaining Voltage	$I_C = 0.2 \text{ A}$ $R_{BE} = 50 \Omega$	110			V
Collector-Emitter Sustaining Voltage	$I_C = 0.2 \text{ A}$ $R_{BE} = 100 \Omega$ $V_{BE} = -1.5 V$	150			V
Collector-Emitter Saturation Voltage	$I_C = 12 \text{ A}$ $I_B = 1.2 \text{ A}$ $I_C = 20 \text{ A}$ $I_B = 5 \text{ A}$			1 2.5	V V
Collector-Emitter Saturation Voltage	I _C = 20 A I _B = 5 A			3.3	V
Base-Emitter Voltage	I _C = 12 A V _{CE} = 5 V			1.8	V
DC Current Gain	I _C = 2 A V _{CE} = 5 V I _C = 12 A V _{CE} = 5 V	50 20		250 100	
Small Signal Current Gain	I _C = 2 A V _{CE} = 10 V f = 5 MHz	12			
Collector-Base Capacitance	I _E = 0 V _{CB} = 10 V f = 1 MHz			300	pF
Rise Time Storage Time Fall Time	$I_C = 12 \text{ A}$ $V_{CC} = 30 \text{ V}$ $I_{B1} = -I_{B2} = 1.2 \text{A}$			0.5 1.5 0.5	μs μs μs
Second Breakdown Collector Current	V _{CE} = 28 V V _{CE} = 45 V	5 0.9			A A
Second Breakdown Energy	$V_{BE} = -4 \ V \ R_{BE} = 20 \ \Omega \ L = 180 \mu H$	13			mJ
	Collector Cut-off Current (V _{BE} = -1.5V) Collector Cut-off Current (I _B = 0) Emitter Cut-off Current (I _C = 0) Collector-Emitter Sustaining Voltage Collector-Emitter Sustaining Voltage Collector-Emitter Sustaining Voltage Collector-Emitter Saturation Voltage Collector-Emitter Saturation Voltage DC Current Gain Small Signal Current Gain Collector-Base Capacitance Rise Time Storage Time Fall Time Second Breakdown Collector Current Second Breakdown	Collector Cut-off Current ($V_{BE} = -1.5V$) Collector Cut-off Current ($V_{CE} = 140 \text{ V}$ V V V V V V V V V V V V V V V V V V	Collector Cut-off Current ($V_{BE} = -1.5V$) Collector Cut-off Current ($I_{B} = 0$) Emitter Cut-off Current ($I_{C} = 0$) Collector-Emitter Sustaining Voltage Collector-Emitter Saturation Voltage IC = 12 A I _B = 1.2 A I _B = 5 A Collector-Emitter Saturation Voltage IC = 20 A I _B = 5 A Collector-Emitter Saturation Voltage Base-Emitter Voltage IC = 12 A V _{CE} = 5 V 50 1C = 12 A V _{CE} = 5 V 20 Small Signal Current Gain IC = 2 A V _{CE} = 5 V 50 20 Small Signal Current Gain IC = 2 A V _{CE} = 10 V f = 5 MHz 12 Collector-Base Capacitance Rise Time Storage Time Fall Time Second Breakdown V _{CE} = 28 V V _{CE} = 45 V 50 99 Second Breakdown V _{CE} = 45 V R _{BE} = 20 Ω L = 180 μ H 13	Collector Cut-off Current ($V_{BE} = -1.5V$) $V_{CE} = 140 \text{ V}$ $V_{CE} = 150 \text{ °C}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 150 \text{ °C}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 150 \text{ °C}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 150 \text{ °C}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 100 \text{ C}$	Collector Cut-off Current (V _{BE} = -1.5V) V _{CE} = 140 V V _{CE} = 150 °C 50 10 Collector Cut-off Current (I _B = 0) V _{CE} = 70 V 20 Emitter Cut-off Current (I _C = 0) V _{EB} = 7 V V _{EB} = 5 V 50 5 Collector-Emitter Sustaining Voltage I _C = 0.2 A 90 Collector-Emitter Sustaining Voltage I _C = 0.2 A R _{BE} = 50 Ω 110 Collector-Emitter Sustaining Voltage I _C = 0.2 A R _{BE} = 100 Ω V _{BE} = -1.5V 150 Collector-Emitter Sustaining Voltage I _C = 12 A I _B = 1.2 A I _B = 5 A 150 2.5 Collector-Emitter Sustaining Voltage I _C = 20 A I _B = 5 A 2.5 2.5 Collector-Emitter Sustaining Voltage I _C = 12 A V _{CE} = 5 V 1.8 2.5 Collector-Emitter Sustaining Voltage I _C = 20 A I _B = 5 A 3.3 3.3 Saturation Voltage I _C = 20 A I _B = 5 A 3.3 3.3 Base-Emitter Voltage I _C = 12 A V _{CE} = 5 V 50 250 Base-Emitter Voltage I _C = 12 A V _{CE} = 5 V 20 100 Small Signal Current Gain I _C = 2 A V _{CE} = 10 V f = 1 MHz 300 300

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
** Pulsed: 0.5 s non repetitive pulse.

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TO-3 MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	11.00		13.10	0.433		0.516
В	0.97		1.15	0.038		0.045
С	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
Е	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
Р	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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